



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	7mΩ @ V _{GS} = 10V	14.1A
30V	10mΩ @ V _{GS} = 4.5V	11.8A
	15mΩ @ V _{GS} = 3.7V	9.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

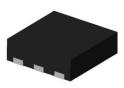
Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

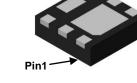
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type F)



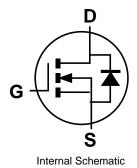
Top View



Bottom View

6 D D 1
5 D D 2
4 S S G 3

Bottom View



Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMT3006LFDF-7	7	3,000
DMT3006LFDF-13	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



6M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	201	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н			,	J	K		L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



6M= Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 9 = 2019)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	1
Code	9	0	1	2	3	4	5	6	l

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V Steady State T _r			I _D	14.1 12.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	80	Α
Continuous Source-Drain Diode Current (Note 6) T _A = +25°C			Is	2	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	25	Α
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	31	mJ

Thermal Characteristics

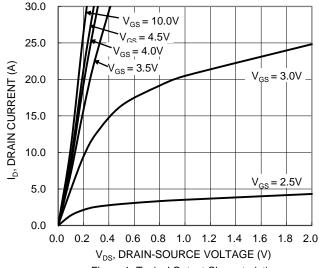
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	155	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R ₀ JA	60	°C/W
Thermal Resistance, Junction to Case (Note 6)	T _C = +25°C	ReJC	6.9	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

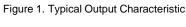
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	1	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (T _J = +25°C)	I _{DSS}	_	I	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			5.8	7		$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.8	10	mΩ	$V_{GS} = 4.5V, I_D = 8A$	
			9.3	15		$V_{GS} = 3.7V, I_D = 5A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V$, $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1,155	_		45)/)/ 0)/	
Output Capacitance	Coss	_	456	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	72	_		1 = 1.0101112	
Gate Resistance	R_{G}	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	8.4	_			
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	16.7	_	nC	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q _{GS}	_	2.2	_	nc nc	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	Q_{GD}	_	3.5	_			
Turn-On Delay Time	t _{D(ON)}	_	3.5	_			
Turn-On Rise Time	t _R	_	5.5	_	20	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	_	ns	$R_G = 3\Omega$, $I_D = 9A$	
Turn-Off Fall Time	t _F	_	4.6	_			
Reverse Recovery Time	t _{RR}	_	19.3	_	ns	1 4 5 4 -11/-14 4000 / 1	
Reverse Recovery Charge	Q_{RR}		8.6	_	nC	I _F = 1.5A, di/dt = 100A/μs	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.
 - 8. Short duration pulse test used to minimize self-heating effect.
 - 9. Guaranteed by design. Not subject to product testing.







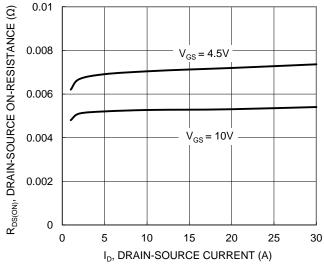


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

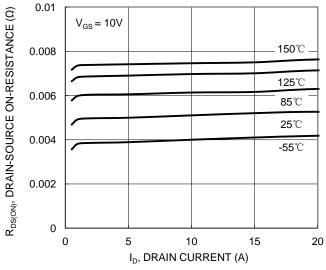
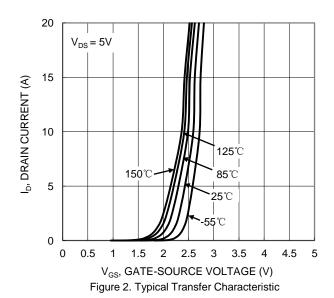


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



0.020 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.018 0.016 0.014 0.012 0.010 $I_{D} = 12A$ 0.008 0.006 0.004 0.002 0.000 2 6 8 10 12 14 16 18 20

V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

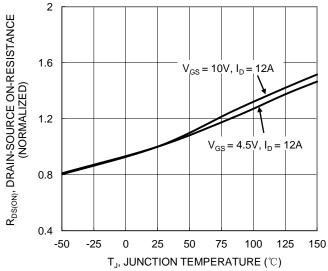


Figure 6. On-Resistance Variation with Temperature





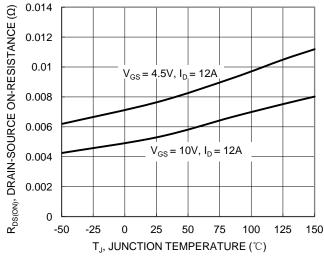


Figure 7. On-Resistance Variation with Temperature

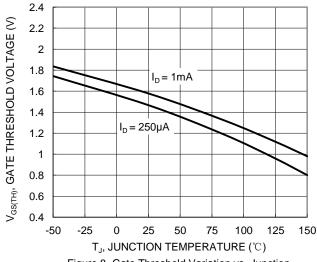


Figure 8. Gate Threshold Variation vs. Junction Temperature

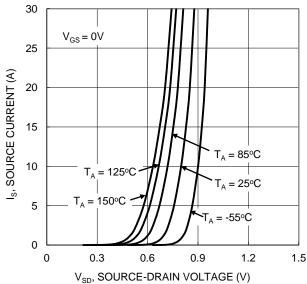
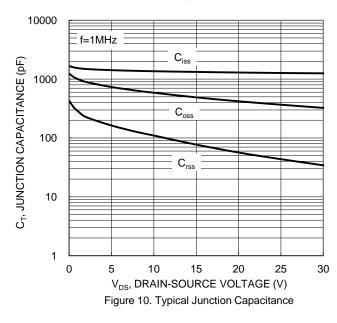
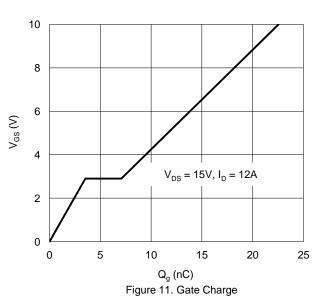
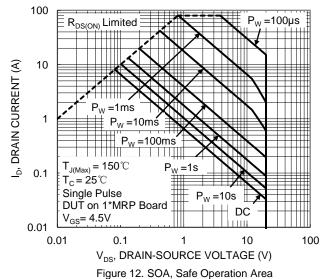


Figure 9. Diode Forward Voltage vs. Current









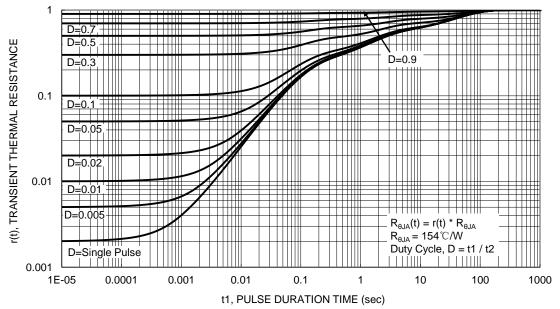


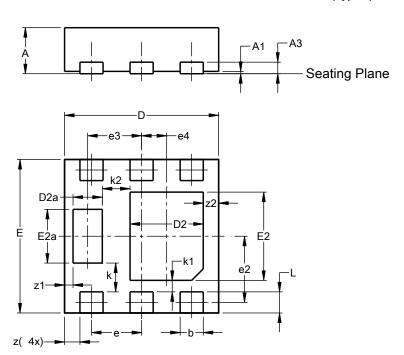
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

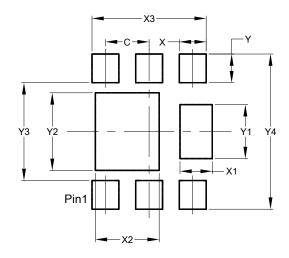


U-DFN2020-6									
	(Type F)								
Dim	Min	Max	Тур						
Α	0.57	0.57 0.63 0.6							
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
Е	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е		0.65 BS	С						
e2).863 BS	SC						
е3		0.70 BS	С						
e4).325 BS	SC						
k		0.37 BS	С						
k1		0.15 BS	С						
k2	0.36 BSC								
L	0.225 0.325 0.275								
Z	0.20 BSC								
z1	0.110 BSC								
z2		0.20 BS	С						
All C	imens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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